N-Channel 12-V (D-S) MOSFET

CHARACTERISTICS

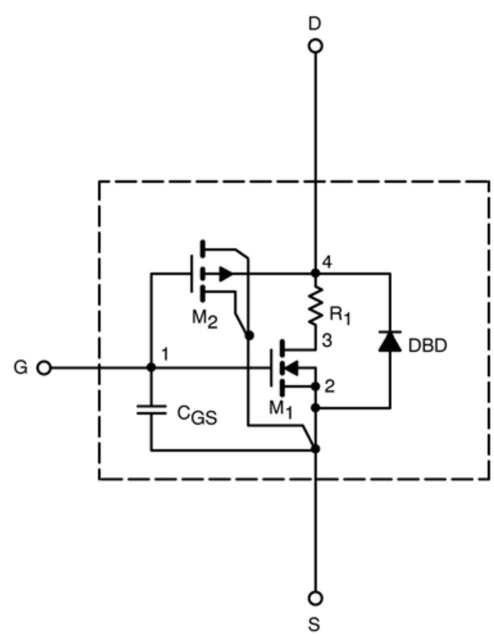
- N-Channel Vertical DMOS
- Macro Model (Subcircuit Model)
- Level 3 MOS
- Apply for both Linear and Switching Application
- Accurate over the −55 to 125°C Temperature Range
- Model the Gate Charge, Transient, and Diode Reverse Recovery Characteristics

DESCRIPTION

The attached spice model describes the typical electrical characteristics of the n-channel vertical DMOS. The subcircuit model is extracted and optimized over the −55 to 125°C temperature ranges under the pulsed 0-V to 5-V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched C_{gd} model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

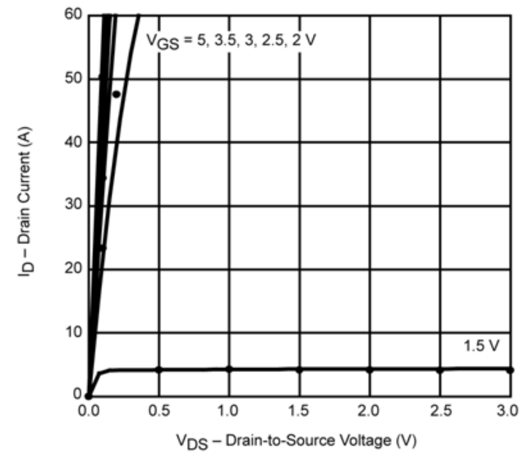
SUBCIRCUIT MODEL SCHEMATIC

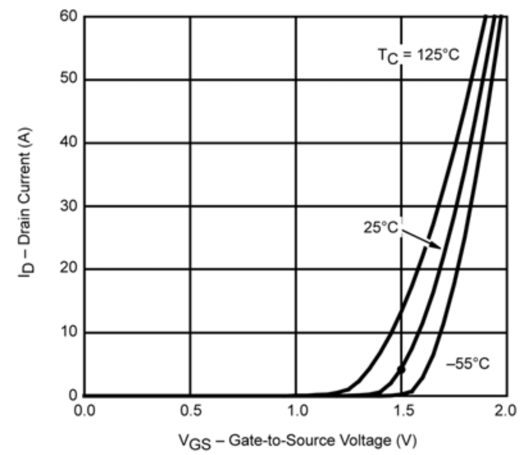


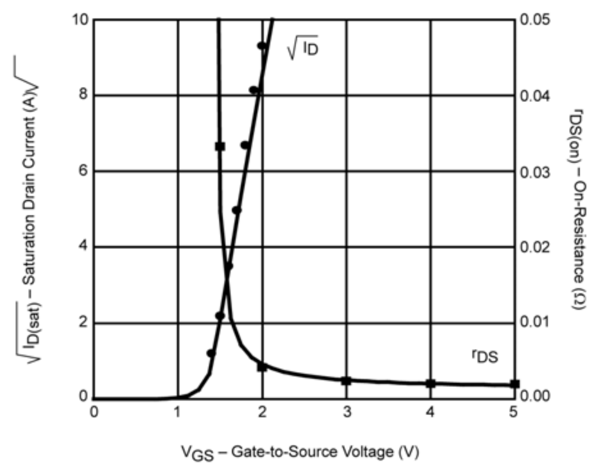
SPECIFICATIONS (T_J = 25°C UNLESS OTHERWISE NOTED)					
Parameter	**Symbol**	**Test Condition**	**Simulated Data**	**Measured Data**	**Unit**
Static					
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = 250 µA	0.91		V
On-State Drain Current[a]	$I_{D(on)}$	$V_{DS} \geq 5$ V, V_{GS} = 4.5 V	1265		A
Drain-Source On-State Resistance[a]	$r_{DS(on)}$	V_{GS} = 4.5 V, I_D = 25 A	0.0019	0.0024	Ω
		V_{GS} = 2.5 V, I_D = 20 A	0.0031	0.0031	
Forward Transconductance[a]	g_{fs}	V_{DS} = 6 V, I_D = 25 A	142	80	S
Diode Forward Voltage[a]	V_{SD}	I_S = 2.9 A, V_{GS} = 0 V	0.76	0.75	V
Dynamic[b]					
Total Gate Charge	Q_g	V_{DS} = 6 V, V_{GS} = 4.5 V, I_D = 25 A	42	40	nC
Gate-Source Charge	Q_{gs}		6.7	6.7	
Gate-Drain Charge	Q_{gd}		9.2	9.2	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 6 V, R_L = 6 Ω $I_D \cong 1$ A, V_{GEN} = 4.5 V, R_G = 6 Ω	41	40	ns
Rise Time	t_r		58	40	
Turn-Off Delay Time	$t_{d(off)}$		66	140	
Fall Time	t_f		118	70	
Source-Drain Reverse Recovery Time	t_{rr}	I_F = 2.9 A, di/dt = 100 A/µs	51	50	

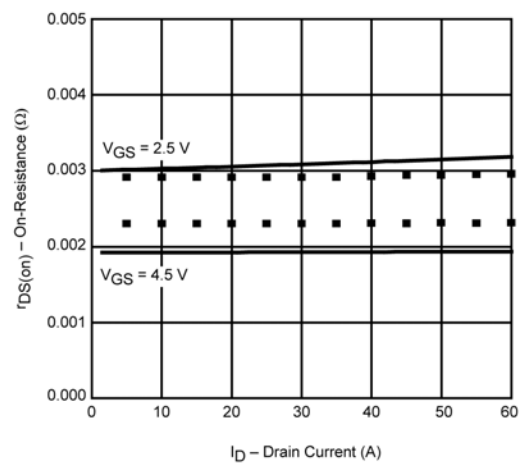
Notes
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2%.
b. Guaranteed by design, not subject to production testing.

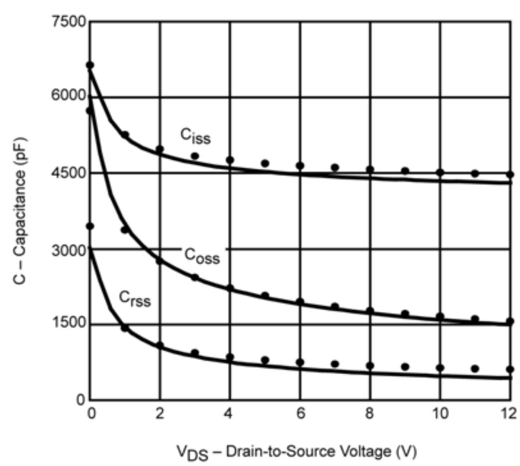
COMPARISON OF MODEL WITH MEASURED DATA (T_J=25°C UNLESS OTHERWISE NOTED)

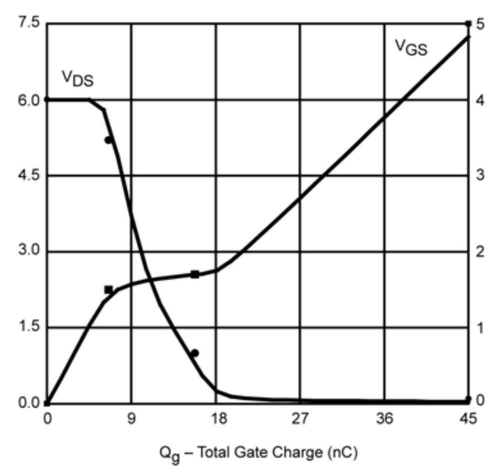












Note: Dots and squares represent measured data.

Disclaimer

All product specifications and data are subject to change without notice.

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